

isc Silicon NPN Power Transistor

2SD111

DESCRIPTION

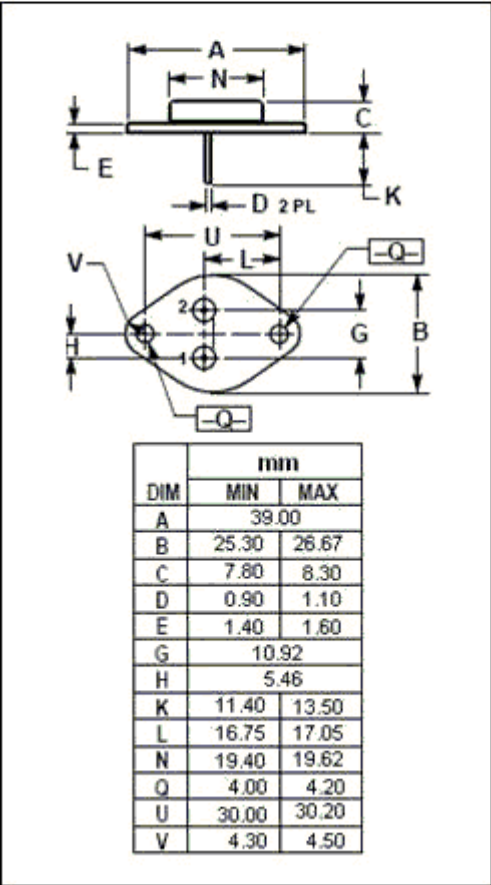
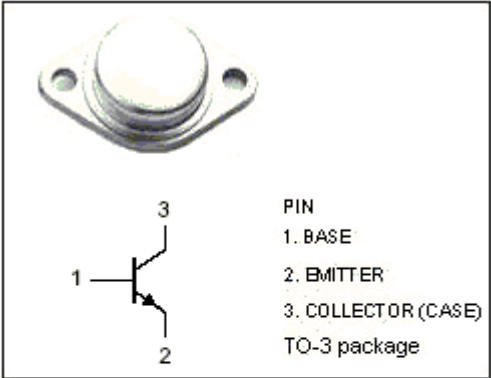
- High Power Dissipation-
: $P_C = 100W @ T_C = 25^{\circ}C$
- High Current Capability-
: $I_C = 10A$

APPLICATIONS

- Designed for power amplifier , power switching ,DC-DC converter and regulator applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current-Continuous	10	A
I_E	Emitter Current-Continuous	-10	A
I_B	Base Current-Continuous	3	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	100	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-65~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SD111****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}$; $R_{BE}=\infty$	80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=50\text{mA}$; $I_C=0$	10			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}$; $I_B=1\text{A}$			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}$; $I_B=1\text{A}$			2.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=50\text{V}$; $I_E=0$			0.5	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=10\text{V}$; $I_C=0$			10	mA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}$; $V_{CE}=5\text{V}$	30		300	
h_{FE-2}	DC Current Gain	$I_C=5\text{A}$; $V_{CE}=5\text{V}$	10			
f_T	Current-Gain—Bandwidth Product	$I_C=1\text{A}$; $V_{CE}=10\text{V}$		1		MHz
C_{OB}	Output Capacitance	$I_E=0$; $V_{CB}=50\text{V}$; $f=1\text{MHz}$		200		pF

◆ **h_{FE-2} Classifications**

R	O	Y
30-90	50-150	100-300